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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Fumio Horiguchi

SERIAL NUMBER: 10/073,339

GROUP: 2824

FILED: February 13, 2002

EXAMINER: TRAN, ANDREW Q

FOR: **MULTI-VALUE MAGNETIC RANDOM ACCESS MEMORY WITH
STACKED TUNNEL MAGNETORESISTANCE (TMR) ELEMENTS**

REQUEST TO CORRECT TITLE OF INVENTION

MAIL STOP ISSUE FEE
COMMISSIONER FOR PATENTS
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SIR:

In the matter of the above-identified application for patent, we hereby request correction of your records to reflect the correct title of the invention. The title of the invention should read as follows: **MULTI-VALUE MAGNETIC RANDOM ACCESS MEMORY WITH STACKED TUNNEL MAGNETORESISTANCE (TMR) ELEMENTS.**

Respectfully Submitted,

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